



# **High Speed SMD Switching Diode**

#### **FEATURES**

- Fast switching device (trr<4.0ns)
- Surface device type mounting
- Matte Tin(Sn) terminal finish
- Pb free version and RoHS compliant





Hermetically Sealed Glass



# ROHS

#### MECHANICAL DATA

- Case: Mini-MELF Package

- High temperature soldering guaranteed: 270°C/10s

- Polarity: Indicated by black cathode band

- Weight: 31mg (approximately)

MAXIMUM RATINGS AND ELECTRICAL CHA	1	·	1
PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation	P <sub>D</sub>	500	mW
Repetitive Peak Reverse Voltage	$V_{RRM}$	75	V
Reverse Voltage	V <sub>R</sub>	75	V
Peak Forward Surge Current (Note 1)	I <sub>FSM</sub>	2	А
Non-Repetitive Peak Forward Current	I <sub>FM</sub>	450	mA
Mean Forward Current	I <sub>F(AV)</sub>	150	mA
Forward Continuous Current	I <sub>F</sub>	150	mA
Repetitive Peak Forward Current	I <sub>FRM</sub>	450	mA
Thermal Resistance (Junction to Ambient) (Note 2)	$R_{ heta JA}$	300	°C/W
Junction and Storage Temperature Range	Tu. Terc	-65 to +175	ိုင

PARAMETER		SYMBOL	MIN	MAX	UNIT
Poverse Preskdown Veltage	I <sub>R</sub> =100μA	$V_{(BR)}$	100	-	V
Reverse Breakdown Voltage	I <sub>R</sub> =5μA		75	-	
Forward Voltage		V <sub>F</sub>	-	-	V
LL4448, LL914B	I <sub>F</sub> =5 mA		0.62	0.72	
LL4148	I <sub>F</sub> =50 mA		-	1	
LL4448, LL914B	I <sub>F</sub> =100 mA		-	1	
Poverse Leekage Current	V <sub>R</sub> =20V	ı	-	25	nA
Reverse Leakage Current	V <sub>R</sub> =75V	I <sub>R</sub>	-	5	μΑ
Junction Capacitance	V <sub>R</sub> =0 f=1.0MHz	CJ	-	4	pF
Reverse Recovery Time	(Note 3)	t <sub>rr</sub>	-	4	ns

Note 1: Test condition: 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)

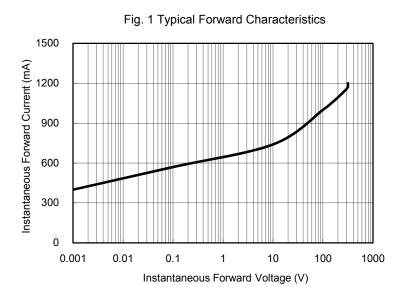
Note 2: Valid provided that electrodes are kept at ambient temperature

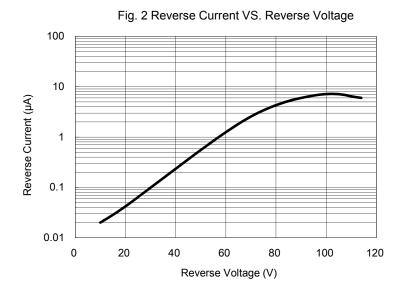
Note 3: Reverse recovery test conditions :  $I_F = I_R = 10 \text{mA}$ ,  $R_L = 100 \Omega$ ,  $I_{RR} = 1 \text{mA}$ 

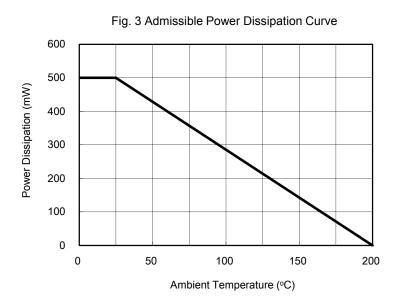


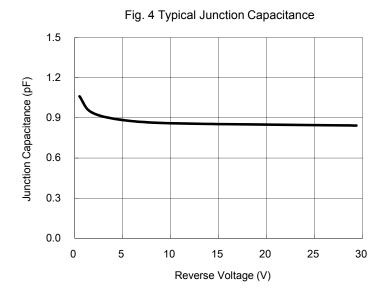
#### RATINGS AND CHARACTERISTICS CURVES

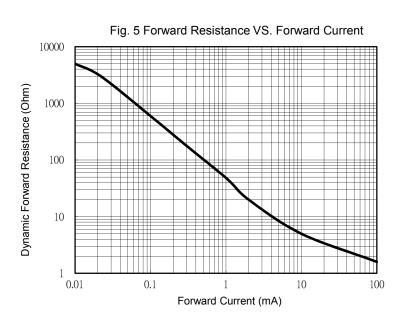
(T<sub>A</sub>=25°C unless otherwise noted)









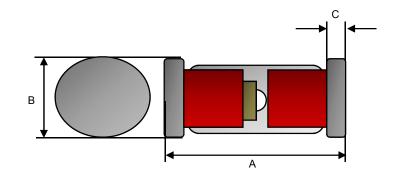




### ORDER INFORMATION (EXAMPLE)

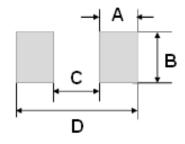


### PACKAGE OUTLINE DIMENSION



DIM.	Unit (mm)		Unit (inch)	
DIIVI.	Min	Max	Min	Max
Α	3.30	3.70	0.130	0.146
В	1.40	1.60	0.055	0.063
С	0.20	0.50	0.008	0.020

### SUGGEST PAD LAYOUT



DIM.	Unit (mm)	Unit (inch)
DIIVI.	Тур.	Тур.
Α	1.25	0.049
В	2.00	0.079
С	2.50	0.098
D	5.00	0.197





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### Taiwan Semiconductor:

<u>LL4148 LL914B LL914B LL4448 LOG LL4148 LOG LL4148 L1 LL4148 L1 LL4448 L1 L1 L14448 L1 L1448 L1 L14448 L1 L1448 L1 L14448 L1 L14448 L1 L14448 L1 L14448 L1 L14448 L1 L1448 L1 L14448 L1 L1448 L1 L14448 L1 L14448 L1 L14448 L1 L14448 L1 L14</u>